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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet of 2

Complete if Known			
Application Number	10/734,294		
Filing Date	December 15, 2003		
First Named Inventor	Seon Yong CHA		
Group Art Unit	2826		
Examiner Name	Thomas L. Dickey		
Attorney Docket Number	40296-0048		

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Examiner Cite No.1	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant	
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¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449A/PTO Complete if Known **Application Number** 10/734,294 INFORMATION DISCLOSURE Filing Date December 15, 2003 STATEMENT BY APPLICANT Seon Yong CHA First Named Inventor 2826 **Group Art Unit** (use as many sheets as necessary) Thomas L. Dickey **Examiner Name** of 2 Attorney Docket Number 40296-0048 Sheet

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Examiner	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
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